

# **MBRD1040**

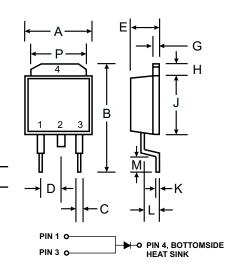
### **10A LOW VF SCHOTTKY BARRIER RECTIFIER**

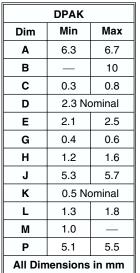
## Features

- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Maximum Junction Temperature Rating
- Very Low Forward Voltage Drop
- Very Low Leakage Current
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- Plastic Material: UL Flammability Classification Rating 94V-0

#### **Mechanical Data**

- Case: DPAK Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: See Diagram
- Marking Information: See Page 2
- Weight: 0.4 grams (approx.)





Note: Pins 1 & 3 must be electrically connected at the printed circuit board.

#### Maximum Ratings @ T<sub>A</sub> = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.

Characteristic	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	40	V	
RMS Reverse Voltage	V <sub>R(RMS)</sub>	28	V	
Average Rectified Output Current (Also see Figure 4)	lo	10	А	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave Superimposed on Rated Load (JEDEC Method)	IFSM	100	А	
Typical Thermal Resistance Junction to Case	R <sub>θJC</sub>	6.0	°C/W	
Typical Thermal Resistance Junction to Ambient	R <sub>0JA</sub>	80	°C/W	
Operating Temperature Range	Tj	-65 to +150	°C	
Storage Temperature Range	T <sub>STG</sub>	-65 to +150	°C	

#### Electrical Characteristics @ T<sub>A</sub> = 25°C unless otherwise specified

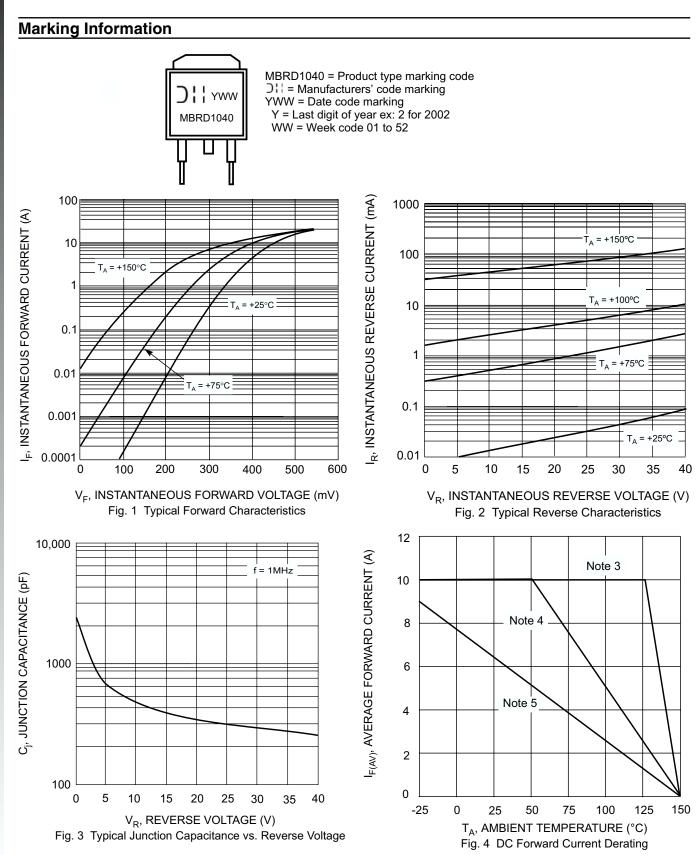
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 1)	V <sub>(BR)R</sub>	40	_	_	V	I <sub>R</sub> = 1mA
Forward Voltage (Note 1)	V <sub>FM</sub>		0.45  0.47	0.49 0.41 0.51	v	$ I_{F} = 8A, T_{S} = 25^{\circ}C \\ I_{F} = 8A, T_{S} = 125^{\circ}C \\ I_{F} = 10A, T_{S} = 25^{\circ}C $
Peak Reverse Current (Note 1)	I <sub>RM</sub>		0.1 12.5	0.3 25	mA	$T_{S} = 25^{\circ}C, V_{R} = 35V$ $T_{S} = 100^{\circ}C, V_{R} = 35V$
Junction Capacitance	Cj	—	700	—	pF	f = 1.0MHz, V <sub>R</sub> = 4.0V DC

Notes: 1. Short duration test pulse used to minimize self-heating effect.

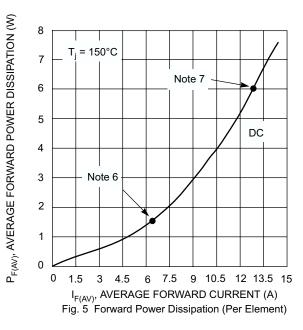
NEW PRODUCT

# Device Packaging Shipping MBRD1040-T DPAK 2500/Tape & Reel

Notes: 2. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.







- Notes: 3.  $T_A = T_{SOLDERING POINT}$ ,  $R_{\theta JC} = 6.0^{\circ}C/W$ ,  $R_{\theta CA} = 0^{\circ}C/W$ .
  - Device mounted on GETEK substrate, 2"x2", 2 oz. copper, double-sided, cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0". R<sub>0JA</sub> in range of 15-30°C/W.
  - Device mounted on FR-4 substrate, 2"x2", 2 oz. copper, single-sided, pad layout as per Diodes Inc. suggested pad layout document AP02001 which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf. R<sub>0JA</sub> in range of 60-75°C/W.
  - 6. Maximum power disspiation when the device is mounted in accordance to the conditions described in Note 5.
  - 7. Maximum power disspation when the device is mounted in accordance to the conditions described in Note 4.